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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	291
Number of Logic Elements/Cells	2910
Total RAM Bits	59904
Number of I/O	104
Number of Gates	-
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	144-LQFP
Supplier Device Package	144-TQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/intel/ep1c3t144c8n

1. Introduction

C51001-1.5

Introduction

The Cyclone® field programmable gate array family is based on a 1.5-V, 0.13-µm, all-layer copper SRAM process, with densities up to 20,060 logic elements (LEs) and up to 288 Kbits of RAM. With features like phase-locked loops (PLLs) for clocking and a dedicated double data rate (DDR) interface to meet DDR SDRAM and fast cycle RAM (FCRAM) memory requirements, Cyclone devices are a cost-effective solution for data-path applications. Cyclone devices support various I/O standards, including LVDS at data rates up to 640 megabits per second (Mbps), and 66- and 33-MHz, 64- and 32-bit peripheral component interconnect (PCI), for interfacing with and supporting ASSP and ASIC devices. Altera also offers new low-cost serial configuration devices to configure Cyclone devices.

Features

The Cyclone device family offers the following features:

- 2,910 to 20,060 LEs, see Table 1–1
- Up to 294,912 RAM bits (36,864 bytes)
- Supports configuration through low-cost serial configuration device
- Support for LVTTL, LVCMOS, SSTL-2, and SSTL-3 I/O standards
- Support for 66- and 33-MHz, 64- and 32-bit PCI standard
- High-speed (640 Mbps) LVDS I/O support
- Low-speed (311 Mbps) LVDS I/O support
- 311-Mbps RSDS I/O support
- Up to two PLLs per device provide clock multiplication and phase shifting
- Up to eight global clock lines with six clock resources available per logic array block (LAB) row
- Support for external memory, including DDR SDRAM (133 MHz), FCRAM, and single data rate (SDR) SDRAM
- Support for multiple intellectual property (IP) cores, including Altera® MegaCore® functions and Altera Megafunctions Partners Program (AMPP℠) megafunctions.

Table 1–1. Cyclone Device Features (Part 1 of 2)

Feature	EP1C3	EP1C4	EP1C6	EP1C12	EP1C20
LEs	2,910	4,000	5,980	12,060	20,060
M4K RAM blocks (128 × 36 bits)	13	17	20	52	64

2. Cyclone Architecture

C51002-1.6

Functional Description

Cyclone® devices contain a two-dimensional row- and column-based architecture to implement custom logic. Column and row interconnects of varying speeds provide signal interconnects between LABs and embedded memory blocks.

The logic array consists of LABs, with 10 LEs in each LAB. An LE is a small unit of logic providing efficient implementation of user logic functions. LABs are grouped into rows and columns across the device. Cyclone devices range between 2,910 to 20,060 LEs.

M4K RAM blocks are true dual-port memory blocks with 4K bits of memory plus parity (4,608 bits). These blocks provide dedicated true dual-port, simple dual-port, or single-port memory up to 36-bits wide at up to 250 MHz. These blocks are grouped into columns across the device in between certain LABs. Cyclone devices offer between 60 to 288 Kbits of embedded RAM.

Each Cyclone device I/O pin is fed by an I/O element (IOE) located at the ends of LAB rows and columns around the periphery of the device. I/O pins support various single-ended and differential I/O standards, such as the 66- and 33-MHz, 64- and 32-bit PCI standard and the LVDS I/O standard at up to 640 Mbps. Each IOE contains a bidirectional I/O buffer and three registers for registering input, output, and output-enable signals. Dual-purpose DQS, DQ, and DM pins along with delay chains (used to phase-align DDR signals) provide interface support with external memory devices such as DDR SDRAM, and FCRAM devices at up to 133 MHz (266 Mbps).

Cyclone devices provide a global clock network and up to two PLLs. The global clock network consists of eight global clock lines that drive throughout the entire device. The global clock network can provide clocks for all resources within the device, such as IOEs, LEs, and memory blocks. The global clock lines can also be used for control signals. Cyclone PLLs provide general-purpose clocking with clock multiplication and phase shifting as well as external outputs for high-speed differential I/O support.

Figure 2–1 shows a diagram of the Cyclone EP1C12 device.

signal. The output registers can be bypassed. Pseudo-asynchronous reading is possible in the simple dual-port mode of M4K blocks by clocking the read enable and read address registers on the negative clock edge and bypassing the output registers.

When configured as RAM or ROM, you can use an initialization file to pre-load the memory contents.

Two single-port memory blocks can be implemented in a single M4K block as long as each of the two independent block sizes is equal to or less than half of the M4K block size.

The Quartus II software automatically implements larger memory by combining multiple M4K memory blocks. For example, two 256×16-bit RAM blocks can be combined to form a 256×32-bit RAM block. Memory performance does not degrade for memory blocks using the maximum number of words allowed. Logical memory blocks using less than the maximum number of words use physical blocks in parallel, eliminating any external control logic that would increase delays. To create a larger high-speed memory block, the Quartus II software automatically combines memory blocks with LE control logic.

Parity Bit Support

The M4K blocks support a parity bit for each byte. The parity bit, along with internal LE logic, can implement parity checking for error detection to ensure data integrity. You can also use parity-size data words to store user-specified control bits. Byte enables are also available for data input masking during write operations.

Shift Register Support

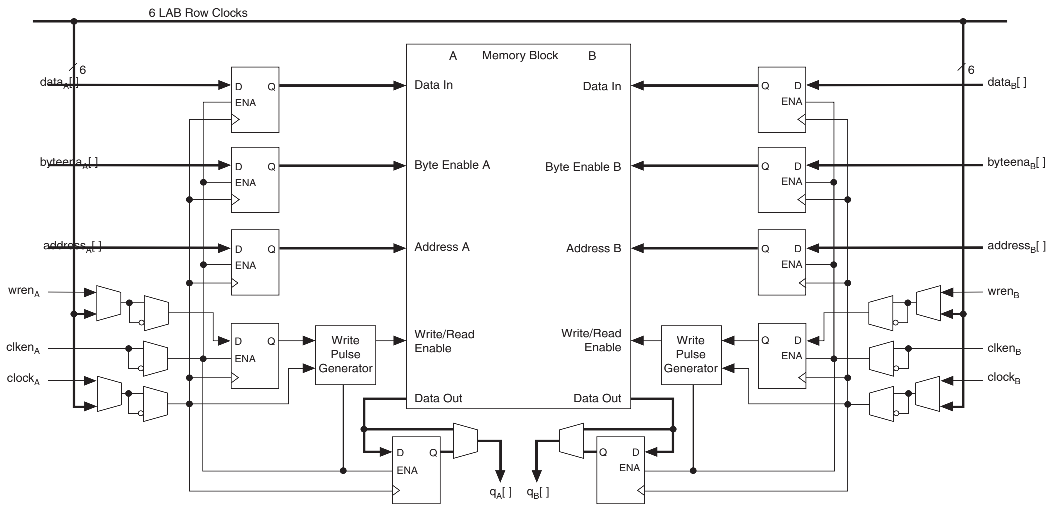
You can configure M4K memory blocks to implement shift registers for DSP applications such as pseudo-random number generators, multi-channel filtering, auto-correlation, and cross-correlation functions. These and other DSP applications require local data storage, traditionally implemented with standard flip-flops, which can quickly consume many logic cells and routing resources for large shift registers. A more efficient alternative is to use embedded memory as a shift register block, which saves logic cell and routing resources and provides a more efficient implementation with the dedicated circuitry.

The size of a $w \times m \times n$ shift register is determined by the input data width (w), the length of the taps (m), and the number of taps (n). The size of a $w \times m \times n$ shift register must be less than or equal to the maximum number of memory bits in the M4K block (4,608 bits). The total number of shift

Independent Clock Mode

The M4K memory blocks implement independent clock mode for true dual-port memory. In this mode, a separate clock is available for each port (ports A and B). Clock A controls all registers on the port A side, while clock B controls all registers on the port B side. Each port, A and B, also supports independent clock enables and asynchronous clear signals for port A and B registers. Figure 2–17 shows an M4K memory block in independent clock mode.

Figure 2–17. Independent Clock Mode *Notes (1), (2)*



Notes to Figure 2–17:

(1) All registers shown have asynchronous clear ports.

(2) Violating the setup or hold time on the address registers could corrupt the memory contents. This applies to both read and write operations.

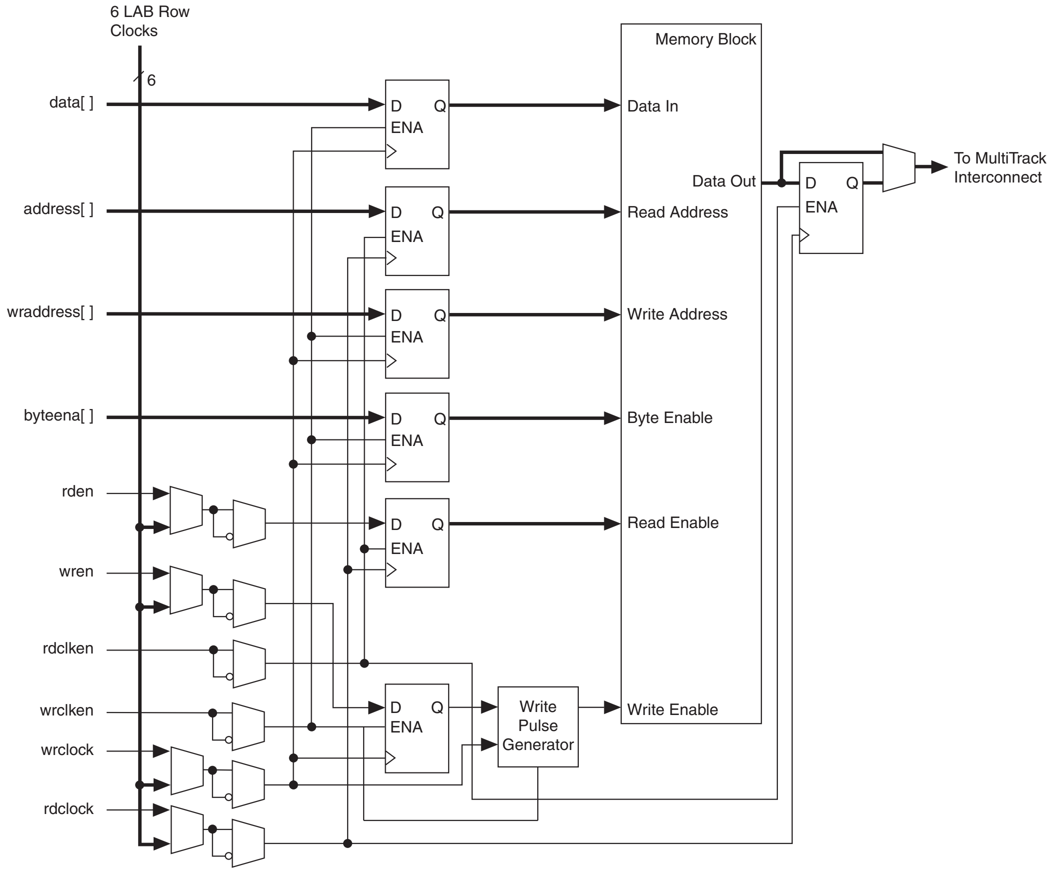
Input/Output Clock Mode

Input/output clock mode can be implemented for both the true and simple dual-port memory modes. On each of the two ports, A or B, one clock controls all registers for inputs into the memory block: data input, `wren`, and address. The other clock controls the block's data output registers. Each memory block port, A or B, also supports independent clock enables and asynchronous clear signals for input and output registers. Figures 2–18 and 2–19 show the memory block in input/output clock mode.

Read/Write Clock Mode

The M4K memory blocks implement read/write clock mode for simple dual-port memory. You can use up to two clocks in this mode. The write clock controls the block's data inputs, `wraddress`, and `wren`. The read clock controls the data output, `rdaddress`, and `rden`. The memory blocks support independent clock enables for each clock and asynchronous clear signals for the read- and write-side registers. Figure 2–20 shows a memory block in read/write clock mode.

Figure 2–20. Read/Write Clock Mode in Simple Dual-Port Mode *Notes (1), (2)*



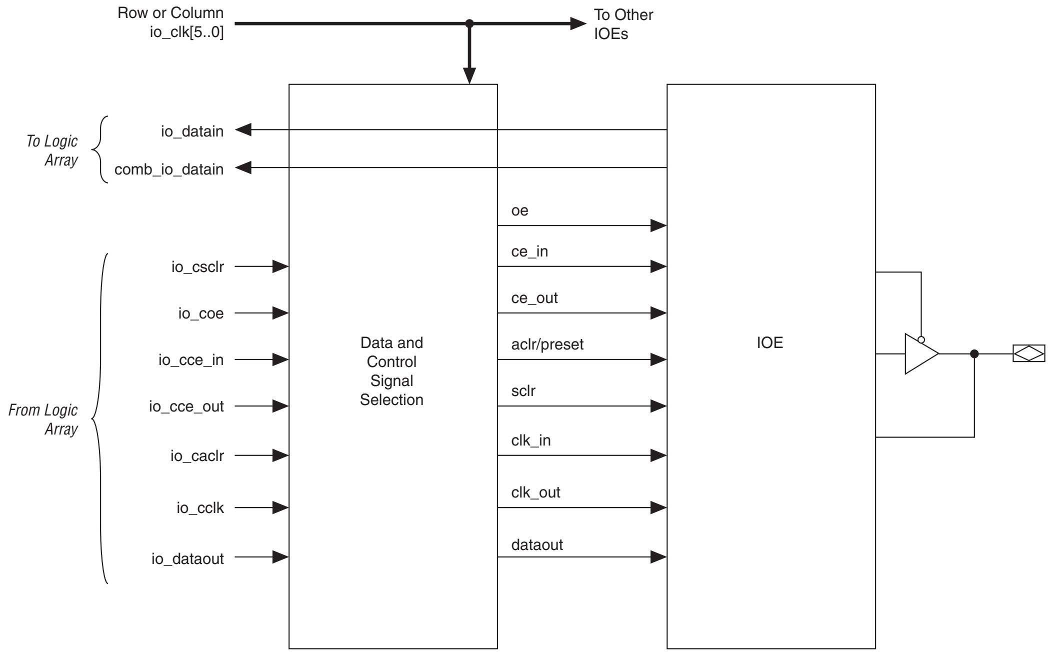
Notes to Figure 2–20:

(1) All registers shown except the rden register have asynchronous clear ports.

(2) Violating the setup or hold time on the address registers could corrupt the memory contents. This applies to both read and write operations.

The pin's datain signals can drive the logic array. The logic array drives the control and data signals, providing a flexible routing resource. The row or column IOE clocks, `io_clk[5..0]`, provide a dedicated routing resource for low-skew, high-speed clocks. The global clock network generates the IOE clocks that feed the row or column I/O regions (see "Global Clock Network and Phase-Locked Loops" on page 2–29). Figure 2–30 illustrates the signal paths through the I/O block.

Figure 2–30. Signal Path through the I/O Block



Each IOE contains its own control signal selection for the following control signals: `oe`, `ce_in`, `ce_out`, `aclr/preset`, `sclr/preset`, `clk_in`, and `clk_out`. Figure 2–31 illustrates the control signal selection.

of the standard. Using minimum settings provides signal slew rate control to reduce system noise and signal overshoot. Table 2–11 shows the possible settings for the I/O standards with drive strength control.

Table 2–11. Programmable Drive Strength Note (1)

I/O Standard	I_{OH}/I_{OL} Current Strength Setting (mA)
LVTTL (3.3 V)	4
	8
	12
	16
	24 (2)
LVCMOS (3.3 V)	2
	4
	8
	12 (2)
LVTTL (2.5 V)	2
	8
	12
	16 (2)
LVTTL (1.8 V)	2
	8
	12 (2)
LVCMOS (1.5 V)	2
	4
	8 (2)

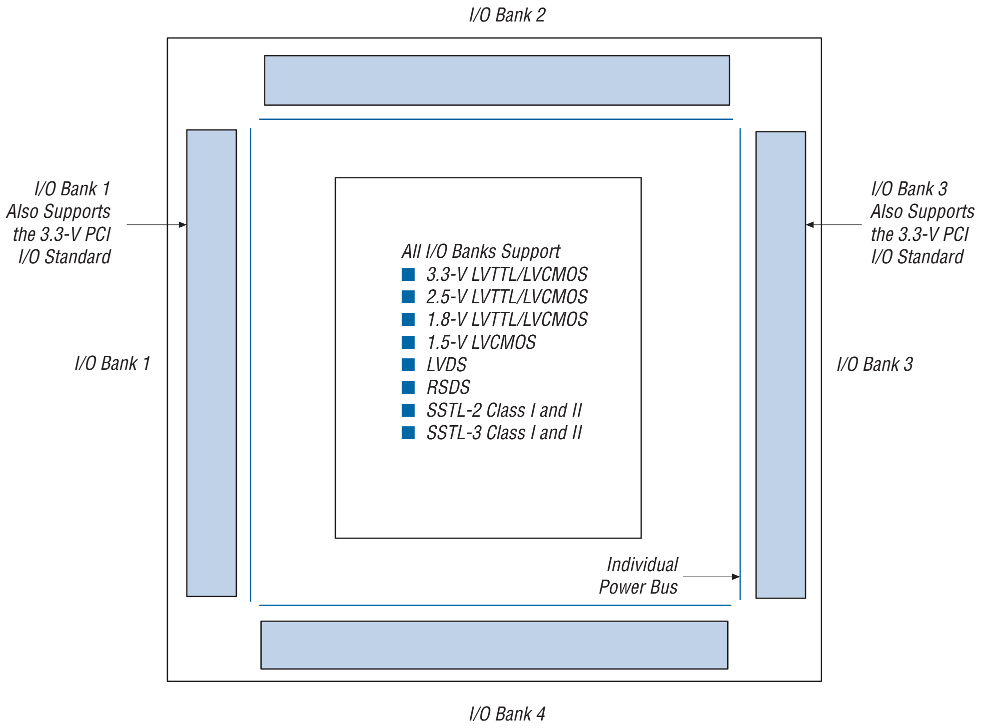
Notes to Table 2–11:
(1) SSTL-3 class I and II, SSTL-2 class I and II, and 3.3-V PCI I/O Standards do not support programmable drive strength.
(2) This is the default current strength setting in the Quartus II software.

Open-Drain Output

Cyclone devices provide an optional open-drain (equivalent to an open-collector) output for each I/O pin. This open-drain output enables the device to provide system-level control signals (e.g., interrupt and write-enable signals) that can be asserted by any of several devices.

and DM pins to support a DDR SDRAM or FCRAM interface. I/O bank 1 can also support a DDR SDRAM or FCRAM interface, however, the configuration input pins in I/O bank 1 must operate at 2.5 V. I/O bank 3 can also support a DDR SDRAM or FCRAM interface, however, all the JTAG pins in I/O bank 3 must operate at 2.5 V.

Figure 2–35. Cyclone I/O Banks *Notes (1), (2)*



Notes to Figure 2–35:

(1) Figure 2–35 is a top view of the silicon die.

(2) Figure 2–35 is a graphic representation only. Refer to the pin list and the Quartus II software for exact pin locations.

Each I/O bank has its own `VCCIO` pins. A single device can support 1.5-V, 1.8-V, 2.5-V, and 3.3-V interfaces; each individual bank can support a different standard with different I/O voltages. Each bank also has dual-purpose `VREF` pins to support any one of the voltage-referenced standards (e.g., SSTL-3) independently. If an I/O bank does not use voltage-referenced standards, the V_{REF} pins are available as user I/O pins.

The Cyclone V_{CCINT} pins must always be connected to a 1.5-V power supply. If the V_{CCINT} level is 1.5 V, then input pins are 1.5-V, 1.8-V, 2.5-V, and 3.3-V tolerant. The V_{CCIO} pins can be connected to either a 1.5-V, 1.8-V, 2.5-V, or 3.3-V power supply, depending on the output requirements. The output levels are compatible with systems of the same voltage as the power supply (i.e., when V_{CCIO} pins are connected to a 1.5-V power supply, the output levels are compatible with 1.5-V systems). When V_{CCIO} pins are connected to a 3.3-V power supply, the output high is 3.3-V and is compatible with 3.3-V or 5.0-V systems. Table 2–14 summarizes Cyclone MultiVolt I/O support.

Table 2–14. Cyclone MultiVolt I/O Support *Note (1)*

V_{CCIO} (V)	Input Signal					Output Signal				
	1.5 V	1.8 V	2.5 V	3.3 V	5.0 V	1.5 V	1.8 V	2.5 V	3.3 V	5.0 V
1.5	✓	✓	✓ (2)	✓ (2)	—	✓	—	—	—	—
1.8	✓	✓	✓ (2)	✓ (2)	—	✓ (3)	✓	—	—	—
2.5	—	—	✓	✓	—	✓ (5)	✓ (5)	✓	—	—
3.3	—	—	✓ (4)	✓	✓ (6)	✓ (7)	✓ (7)	✓ (7)	✓	✓ (8)

Notes to Table 2–14:
(1) The PCI clamping diode must be disabled to drive an input with voltages higher than V_{CCIO}.
(2) When V_{CCIO} = 1.5-V or 1.8-V and a 2.5-V or 3.3-V input signal feeds an input pin, higher pin leakage current is expected. Turn on **Allow voltage overdrive for LVTTL / LVCMOS input pins** in the Assignments > Device > Device and Pin Options > Pin Placement tab when a device has this I/O combinations.
(3) When V_{CCIO} = 1.8-V, a Cyclone device can drive a 1.5-V device with 1.8-V tolerant inputs.
(4) When V_{CCIO} = 3.3-V and a 2.5-V input signal feeds an input pin, the V_{CCIO} supply current will be slightly larger than expected.
(5) When V_{CCIO} = 2.5-V, a Cyclone device can drive a 1.5-V or 1.8-V device with 2.5-V tolerant inputs.
(6) Cyclone devices can be 5.0-V tolerant with the use of an external resistor and the internal PCI clamp diode.
(7) When V_{CCIO} = 3.3-V, a Cyclone device can drive a 1.5-V, 1.8-V, or 2.5-V device with 3.3-V tolerant inputs.
(8) When V_{CCIO} = 3.3-V, a Cyclone device can drive a device with 5.0-V LVTTL inputs but not 5.0-V LVCMOS inputs.

Power Sequencing and Hot Socketing

Because Cyclone devices can be used in a mixed-voltage environment, they have been designed specifically to tolerate any possible power-up sequence. Therefore, the V_{CCIO} and V_{CCINT} power supplies may be powered in any order.

Signals can be driven into Cyclone devices before and during power up without damaging the device. In addition, Cyclone devices do not drive out during power up. Once operating conditions are reached and the device is configured, Cyclone devices operate as specified by the user.

3. Configuration and Testing

C51003-1.4

IEEE Std. 1149.1 (JTAG) Boundary Scan Support

All Cyclone® devices provide JTAG BST circuitry that complies with the IEEE Std. 1149.1a-1990 specification. JTAG boundary-scan testing can be performed either before or after, but not during configuration. Cyclone devices can also use the JTAG port for configuration together with either the Quartus® II software or hardware using either Jam Files (**.jam**) or Jam Byte-Code Files (**.jbc**).

Cyclone devices support reconfiguring the I/O standard settings on the IOE through the JTAG BST chain. The JTAG chain can update the I/O standard for all input and output pins any time before or during user mode. Designers can use this ability for JTAG testing before configuration when some of the Cyclone pins drive or receive from other devices on the board using voltage-referenced standards. Since the Cyclone device might not be configured before JTAG testing, the I/O pins might not be configured for appropriate electrical standards for chip-to-chip communication. Programming those I/O standards via JTAG allows designers to fully test I/O connection to other devices.

The JTAG pins support 1.5-V/1.8-V or 2.5-V/3.3-V I/O standards. The TDO pin voltage is determined by the V_{CCIO} of the bank where it resides. The bank V_{CCIO} selects whether the JTAG inputs are 1.5-V, 1.8-V, 2.5-V, or 3.3-V compatible.

Cyclone devices also use the JTAG port to monitor the operation of the device with the SignalTap® II embedded logic analyzer. Cyclone devices support the JTAG instructions shown in Table 3–1.

Table 3–1. Cyclone JTAG Instructions (Part 1 of 2)

JTAG Instruction	Instruction Code	Description
SAMPLE/PRELOAD	00 0000 0101	Allows a snapshot of signals at the device pins to be captured and examined during normal device operation, and permits an initial data pattern to be output at the device pins. Also used by the SignalTap II embedded logic analyzer.
EXTEST *(1)*	00 0000 0000	Allows the external circuitry and board-level interconnects to be tested by forcing a test pattern at the output pins and capturing test results at the input pins.
BYPASS	11 1111 1111	Places the 1-bit bypass register between the TDI and TDO pins, which allows the BST data to pass synchronously through selected devices to adjacent devices during normal device operation.

Table 3–1. Cyclone JTAG Instructions (Part 2 of 2)

JTAG Instruction	Instruction Code	Description
USERCODE	00 0000 0111	Selects the 32-bit USERCODE register and places it between the TDI and TDO pins, allowing the USERCODE to be serially shifted out of TDO.
IDCODE	00 0000 0110	Selects the IDCODE register and places it between TDI and TDO, allowing the IDCODE to be serially shifted out of TDO.
HIGHZ *(1)*	00 0000 1011	Places the 1-bit bypass register between the TDI and TDO pins, which allows the BST data to pass synchronously through selected devices to adjacent devices during normal device operation, while tri-stating all of the I/O pins.
CLAMP *(1)*	00 0000 1010	Places the 1-bit bypass register between the TDI and TDO pins, which allows the BST data to pass synchronously through selected devices to adjacent devices during normal device operation while holding I/O pins to a state defined by the data in the boundary-scan register.
ICR instructions	—	Used when configuring a Cyclone device via the JTAG port with a MasterBlaster™ or ByteBlasterMV™ download cable, or when using a Jam File or Jam Byte-Code File via an embedded processor.
PULSE_NCONFIG	00 0000 0001	Emulates pulsing the nCONFIG pin low to trigger reconfiguration even though the physical pin is unaffected.
CONFIG_IO	00 0000 1101	Allows configuration of I/O standards through the JTAG chain for JTAG testing. Can be executed before, after, or during configuration. Stops configuration if executed during configuration. Once issued, the CONFIG_IO instruction will hold nSTATUS low to reset the configuration device. nSTATUS is held low until the device is reconfigured.
SignalTap II instructions	—	Monitors internal device operation with the SignalTap II embedded logic analyzer.

Note to Table 3–1:

(1) Bus hold and weak pull-up resistor features override the high-impedance state of HIGHZ, CLAMP, and EXTEST.

In the Quartus II software, there is an Auto Usercode feature where you can choose to use the checksum value of a programming file as the JTAG user code. If selected, the checksum is automatically loaded to the USERCODE register. Choose Assignments > Device > Device and Pin Options > General. Turn on **Auto Usercode**.

4. DC and Switching Characteristics

C51004-1.7

Operating Conditions

Cyclone® devices are offered in both commercial, industrial, and extended temperature grades. However, industrial-grade and extended-temperature-grade devices may have limited speed-grade availability.

Tables 4–1 through 4–16 provide information on absolute maximum ratings, recommended operating conditions, DC operating conditions, and capacitance for Cyclone devices.

Table 4–1. Cyclone Device Absolute Maximum Ratings *Notes (1), (2)*

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V_{CCINT}	Supply voltage	With respect to ground *(3)*	–0.5	2.4	V
V_{CCIO}			–0.5	4.6	V
V_{CCA}	Supply voltage	With respect to ground *(3)*	–0.5	2.4	V
V_I	DC input voltage		–0.5	4.6	V
I_{OUT}	DC output current, per pin		–25	25	mA
T_{STG}	Storage temperature	No bias	–65	150	°C
T_{AMB}	Ambient temperature	Under bias	–65	135	°C
T_J	Junction temperature	BGA packages under bias	—	135	°C

Table 4–2. Cyclone Device Recommended Operating Conditions (Part 1 of 2)

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V_{CCINT}	Supply voltage for internal logic and input buffers	*(4)*	1.425	1.575	V
V_{CCIO}	Supply voltage for output buffers, 3.3-V operation	*(4)*	3.00	3.60	V
	Supply voltage for output buffers, 2.5-V operation	*(4)*	2.375	2.625	V
	Supply voltage for output buffers, 1.8-V operation	*(4)*	1.71	1.89	V
	Supply voltage for output buffers, 1.5-V operation	*(4)*	1.4	1.6	V
V_I	Input voltage	*(3)*, *(5)*	–0.5	4.1	V

Table 4–2. Cyclone Device Recommended Operating Conditions (Part 2 of 2)

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V_O	Output voltage		0	V_{CCIO}	V
T_J	Operating junction temperature	For commercial use	0	85	° C
		For industrial use	–40	100	° C
		For extended-temperature use	–40	125	° C

Table 4–3. Cyclone Device DC Operating Conditions *Note (6)*

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Unit
I_I	Input pin leakage current	$V_I = V_{CCIOmax}$ to 0 V *(8)*	–10	—	10	μA
I_{OZ}	Tri-stated I/O pin leakage current	$V_O = V_{CCIOmax}$ to 0 V *(8)*	–10	—	10	μA
I_{CC0}	V_{CC} supply current (standby) (All M4K blocks in power-down mode) *(7)*	EP1C3	—	4	—	mA
		EP1C4	—	6	—	mA
		EP1C6	—	6	—	mA
		EP1C12	—	8	—	mA
		EP1C20	—	12	—	mA
R_{CONF} *(9)*	Value of I/O pin pull-up resistor before and during configuration	$V_I = 0$ V; $V_{CCIO} = 3.3$ V	15	25	50	kΩ
		$V_I = 0$ V; $V_{CCIO} = 2.5$ V	20	45	70	kΩ
		$V_I = 0$ V; $V_{CCIO} = 1.8$ V	30	65	100	kΩ
		$V_I = 0$ V; $V_{CCIO} = 1.5$ V	50	100	150	kΩ
	Recommended value of I/O pin external pull-down resistor before and during configuration	—	—	1	2	kΩ

Table 4–4. LVTTL Specifications

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V_{CCIO}	Output supply voltage	—	3.0	3.6	V
V_{IH}	High-level input voltage	—	1.7	4.1	V
V_{IL}	Low-level input voltage	—	–0.5	0.7	V
V_{OH}	High-level output voltage	$I_{OH} = -4$ to -24 mA *(11)*	2.4	—	V
V_{OL}	Low-level output voltage	$I_{OL} = 4$ to 24 mA *(11)*	—	0.45	V

Table 4–5. LVCMOS Specifications

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V_{CCIO}	Output supply voltage	—	3.0	3.6	V
V_{IH}	High-level input voltage	—	1.7	4.1	V
V_{IL}	Low-level input voltage	—	–0.5	0.7	V
V_{OH}	High-level output voltage	V_{CCIO} = 3.0, I_{OH} = –0.1 mA	V_{CCIO} – 0.2	—	V
V_{OL}	Low-level output voltage	V_{CCIO} = 3.0, I_{OL} = 0.1 mA	—	0.2	V

Table 4–6. 2.5-V I/O Specifications

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V_{CCIO}	Output supply voltage	—	2.375	2.625	V
V_{IH}	High-level input voltage	—	1.7	4.1	V
V_{IL}	Low-level input voltage	—	–0.5	0.7	V
V_{OH}	High-level output voltage	I_{OH} = –0.1 mA	2.1	—	V
		I_{OH} = –1 mA	2.0	—	V
		I_{OH} = –2 to –16 mA *(11)*	1.7	—	V
V_{OL}	Low-level output voltage	I_{OL} = 0.1 mA	—	0.2	V
		I_{OH} = 1 mA	—	0.4	V
		I_{OH} = 2 to 16 mA *(11)*	—	0.7	V

Table 4–7. 1.8-V I/O Specifications

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V_{CCIO}	Output supply voltage	—	1.65	1.95	V
V_{IH}	High-level input voltage	—	0.65 × V_{CCIO}	2.25 *(12)*	V
V_{IL}	Low-level input voltage	—	–0.3	0.35 × V_{CCIO}	V
V_{OH}	High-level output voltage	I_{OH} = –2 to –8 mA *(11)*	V_{CCIO} – 0.45	—	V
V_{OL}	Low-level output voltage	I_{OL} = 2 to 8 mA *(11)*	—	0.45	V

Table 4–13. SSTL-3 Class I Specifications (Part 2 of 2)

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Unit
V_{REF}	Reference voltage	—	1.3	1.5	1.7	V
V_{IH}	High-level input voltage	—	V_{REF} + 0.2	—	V_{CCIO} + 0.3	V
V_{IL}	Low-level input voltage	—	–0.3	—	V_{REF} – 0.2	V
V_{OH}	High-level output voltage	I_{OH} = –8 mA *(11)*	V_{TT} + 0.6	—	—	V
V_{OL}	Low-level output voltage	I_{OL} = 8 mA *(11)*	—	—	V_{TT} – 0.6	V

Table 4–14. SSTL-3 Class II Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Unit
V_{CCIO}	Output supply voltage	—	3.0	3.3	3.6	V
V_{TT}	Termination voltage	—	V_{REF} – 0.05	V_{REF}	V_{REF} + 0.05	V
V_{REF}	Reference voltage	—	1.3	1.5	1.7	V
V_{IH}	High-level input voltage	—	V_{REF} + 0.2	—	V_{CCIO} + 0.3	V
V_{IL}	Low-level input voltage	—	–0.3	—	V_{REF} – 0.2	V
V_{OH}	High-level output voltage	I_{OH} = –16 mA *(11)*	V_{TT} + 0.8	—	—	V
V_{OL}	Low-level output voltage	I_{OL} = 16 mA *(11)*	—	—	V_{TT} – 0.8	V

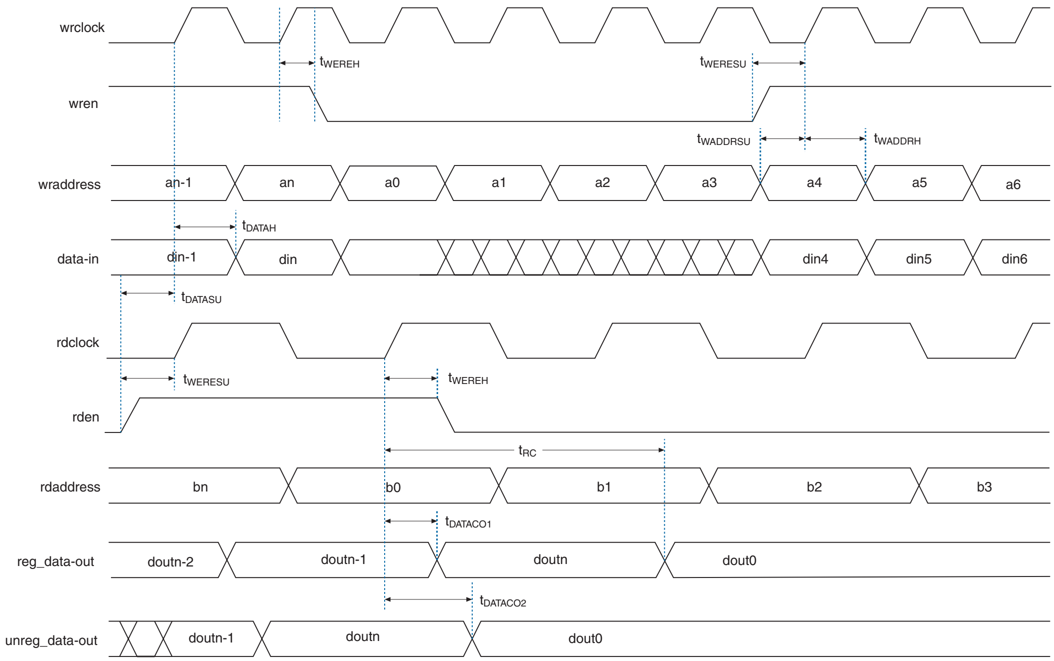
Table 4–15. Bus Hold Parameters

Parameter	Conditions	V_{CCIO} Level								Unit
		1.5 V		1.8 V		2.5 V		3.3 V		
		Min	Max	Min	Max	Min	Max	Min	Max	
Low sustaining current	$V_{IN} > V_{IL}$ (maximum)	—	—	30	—	50	—	70	—	µA
High sustaining current	$V_{IN} < V_{IH}$ (minimum)	—	—	–30	—	–50	—	–70	—	µA
Low overdrive current	0 V < V_{IN} < V_{CCIO}	—	—	—	200	—	300	—	500	µA
High overdrive current	0 V < V_{IN} < V_{CCIO}	—	—	—	–200	—	–300	—	–500	µA

Table 4–24. Routing Delay Internal Timing Microparameter Descriptions	
Symbol	**Parameter**
t_{R4}	Delay for an R4 line with average loading; covers a distance of four LAB columns
t_{C4}	Delay for an C4 line with average loading; covers a distance of four LAB rows
t_{LOCAL}	Local interconnect delay

Figure 4–1 shows the memory waveforms for the M4K timing parameters shown in Table 4–23.

Figure 4–1. Dual-Port RAM Timing Microparameter Waveform



Internal timing parameters are specified on a speed grade basis independent of device density. Tables 4–25 through 4–28 show the internal timing microparameters for LEs, IOEs, TriMatrix memory structures, DSP blocks, and MultiTrack interconnects.

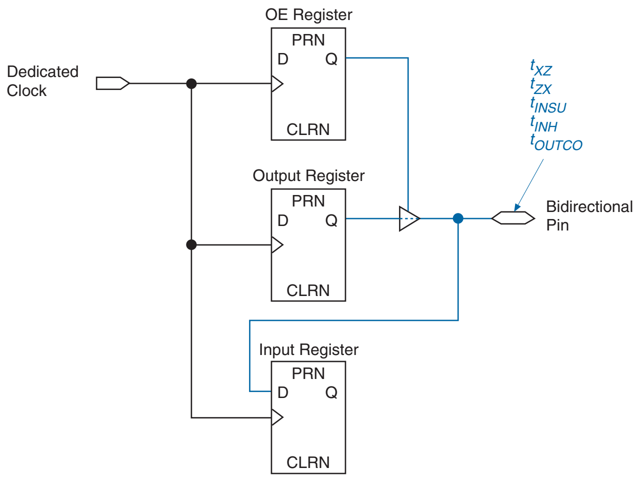
Table 4–25. LE Internal Timing Microparameters

Symbol	-6		-7		-8		Unit
	Min	Max	Min	Max	Min	Max	
t_{SU}	29	—	33	—	37	—	ps
t_H	12	—	13	—	15	—	ps
t_{CO}	—	173	—	198	—	224	ps
t_{LUT}	—	454	—	522	—	590	ps
t_{CLR}	129	—	148	—	167	—	ps
t_{PRE}	129	—	148	—	167	—	ps
t_{CLKHL}	1,234	—	1,562	—	1,818	—	ps

Table 4–26. IOE Internal Timing Microparameters

Symbol	-6		-7		-8		Unit
	Min	Max	Min	Max	Min	Max	
t_{SU}	348	—	400	—	452	—	ps
t_H	0	—	0	—	0	—	ps
t_{CO}	—	511	—	587	—	664	ps
$t_{PIN2COMBOUT\_R}$	—	1,130	—	1,299	—	1,469	ps
$t_{PIN2COMBOUT\_C}$	—	1,135	—	1,305	—	1,475	ps
$t_{COMBIN2PIN\_R}$	—	2,627	—	3,021	—	3,415	ps
$t_{COMBIN2PIN\_C}$	—	2,615	—	3,007	—	3,399	ps
t_{CLR}	280	—	322	—	364	—	ps
t_{PRE}	280	—	322	—	364	—	ps
t_{CLKHL}	1,234	—	1,562	—	1,818	—	ps

Figure 4–2. External Timing in Cyclone Devices



All external I/O timing parameters shown are for 3.3-V LVTTL I/O standard with the maximum current strength and fast slew rate. For external I/O timing using standards other than LVTTL or for different current strengths, use the I/O standard input and output delay adders in Tables 4–40 through 4–44.

Table 4–29 shows the external I/O timing parameters when using global clock networks.

Table 4–29. Cyclone Global Clock External I/O Timing Parameters Notes (1), (2) **(Part 1 of 2)**

Symbol	Parameter	Conditions
t_{INSU}	Setup time for input or bidirectional pin using IOE input register with global clock fed by `CLK` pin	—
t_{INH}	Hold time for input or bidirectional pin using IOE input register with global clock fed by `CLK` pin	—
t_{OUTCO}	Clock-to-output delay output or bidirectional pin using IOE output register with global clock fed by `CLK` pin	C_{LOAD} = 10 pF
$t_{INSUPLL}$	Setup time for input or bidirectional pin using IOE input register with global clock fed by Enhanced PLL with default phase setting	—
t_{INHPLL}	Hold time for input or bidirectional pin using IOE input register with global clock fed by enhanced PLL with default phase setting	—

July 2003 v1.1	Updated timing information. Timing finalized for EP1C6 and EP1C20 devices. Updated performance information. Added PLL Timing section.	—
May 2003 v1.0	Added document to Cyclone Device Handbook.	—